

Notice of References Cited	Application/Control No.	Applicant(s)/Patent Under Reexamination LINGUNIS ET AL.
	Examiner Asok K. Sarkar	Art Unit 2829

U.S. PATENT DOCUMENTS

*	Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
A	US-			
B	US-			
C	US-			
D	US-			
E	US-			
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FOREIGN PATENT DOCUMENTS

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NON-PATENT DOCUMENTS

*	Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)		
U	Huang et al., "Very Low Defects and High Performance Ge – On – Insulator p – MOSFETs with Al2O3 Gate Dielectrics", 2003 Symposium on VLSI Technology Digest of technical papers, p 119 – 120 (10 – 12 June, 2003).		
V			
W			
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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